

Title (en)

CREATION OF DIELECTRICALLY INSULATING SOI-TECHNOLOGICAL TRENCHES COMPRISING ROUNDED EDGES FOR ALLOWING HIGHER VOLTAGES

Title (de)

ERZEUGUNG VON DIELEKTRISCH ISOLIERENDEN GRAEBEN DER SOI-TECHNOLOGIE MIT ABGERUNDETEN KANTEN FUER HOEHERE SPANNUNGEN

Title (fr)

PRODUCTION DE TRANCHEES A EFFET ISOLANT DIELECTRIQUE RELEVANT DE LA TECHNOLOGIE DE SILICIUM SUR ISOLANT, AVEC DES ARETES ARRONDIES POUR DES TENSIONS SUPERIEURES

Publication

**EP 1735827 A1 20061227 (DE)**

Application

**EP 05732412 A 20050407**

Priority

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Abstract (en)

[origin: WO2005098936A1] The aim of the invention is to integrate low-voltage logic elements and high-voltage power elements in one and the same silicon circuit. Said aim is achieved by dielectrically insulating chip regions having different potentials from each other with the aid of isolating trenches (10). In order to prevent voltage rises at sharp edges on the bottom of the isolating trenches, said edges are rounded in a simple process, part of the insulating layer (2) being isotropically etched.

IPC 8 full level

**H01L 21/762** (2006.01)

CPC (source: EP US)

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Citation (search report)

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